

General Description

This MOSFET uses SGT technology to provide excellent $R_{DS(ON)}$, low gate charge and fast switching characteristics. This device is suitable for use as a wide variety of applications.

Features

- Low gate charge
- 100% UIS tested, 100% DVDS tested
- High power and current handing capability
- Lead free product is acquired

Applications

- DC/DC converter
- Load switching, quick/wireless charging, motor driving



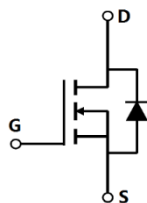
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(ON), max} @ V_{GS}=10V$	2.2	$m\Omega$

Marking Information

Product Name	Package	Marking
SFS04R022GF	PDFN5X6	SFS04R022G

Package & Pin information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	40	V
Gate-source voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	160	A
Pulsed Drain Current ¹⁾	$I_{D,pulse}$	640	A
Power Dissipation	P_D	96	W
Single pulsed avalanche energy ²⁾	E_{AS}	336	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-ambient	$R_{\theta JC}$	1.3	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	40			V	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	1		2.5	V	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		1.6	2.2	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=20\text{ A}$
Drain-source on-state resistance	$R_{DS(ON)}$		2.3	3.2	$\text{m}\Omega$	$V_{GS}=4.5\text{ V}, I_D=20\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$
				-100		$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=40\text{ V}, V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		2645		pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1.0\text{ MHz}$
Output capacitance	C_{oss}		1718		pF	
Reverse transfer capacitance	C_{rss}		102		pF	
Gate resistance	R_g		2.3		Ω	$V_{GS}=0\text{ V}$, $V_{DS}=0\text{ V}$, $f=1.0\text{ MHz}$
Turn-on Delay Time	$t_{d(on)}$		15.2		ns	$V_{GS}=10\text{ V}$, $V_{DS}=20\text{ V}$, $R_L=1\text{ }\Omega$, $R_{GEN}=3\text{ }\Omega$
Turn-on Rise Time	t_r		7.6		ns	
Turn-Off Delay Time	$t_{d(off)}$		48.4		ns	
Turn-Off Fall Time	t_f		13.6		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total Gate Charge	Q_g		51.8		nC	$V_{GS}=10\text{ V}$, $V_{DS}=20\text{ V}$, $I_D=20\text{ A}$
Gate-Source Charge	Q_{gs}		10		nC	
Gate-Drain Charge	Q_{gd}		7.8		nC	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Source drain current (Body Diode)	I_{SD}			165	A	$T_A=25^\circ\text{C}$
Diode forward voltage ³⁾	V_{SD}			1.2	V	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$
Reverse Recovery Time	t_{rr}		43.8		ns	$I_F=20\text{ A}$, $di/dt=100\text{ A/us}$
Reverse Recovery Charge	Q_{rr}		32.6		nC	

Note: 1) Pulse width limited by maximum allowable junction temperature.
 2) EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=40\text{ V}$, $V_G=10\text{ V}$, $R_g=25\text{ }\Omega$, $L=0.5\text{ mH}$.
 3) Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

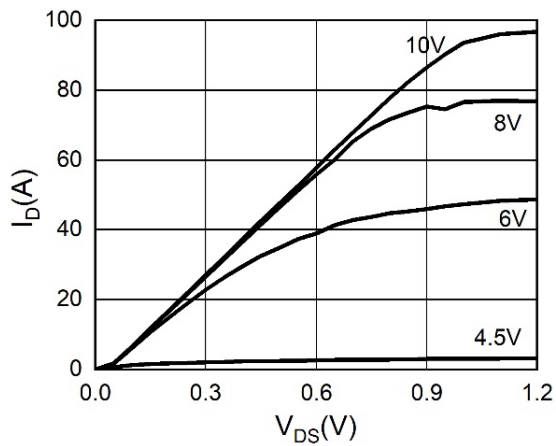


Figure 1. Typ. output characteristics

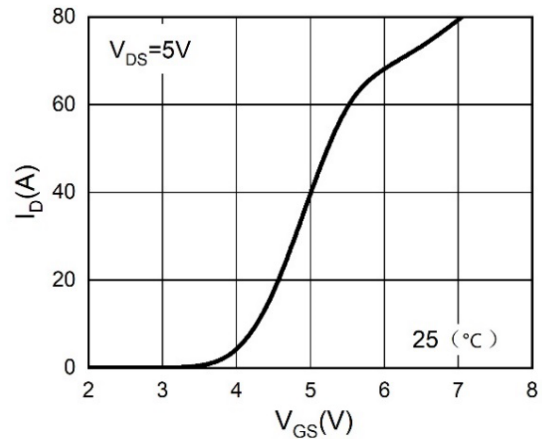


Figure 2. Typ. transfer characteristics

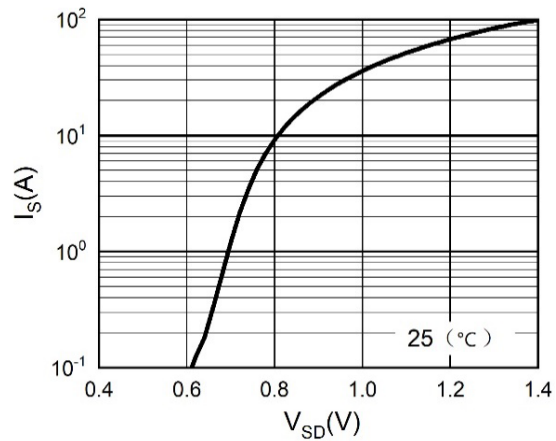


Figure 3. Body-diode Characteristics

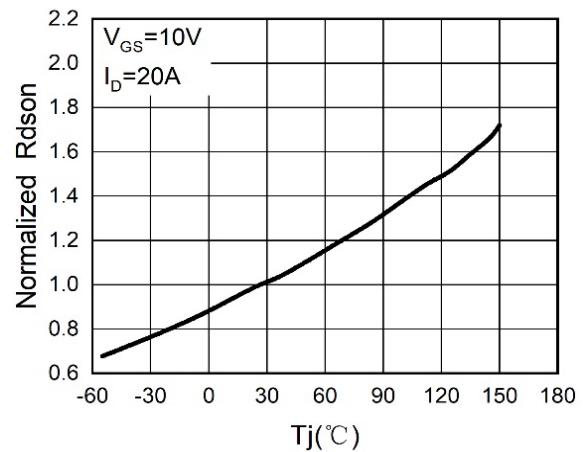


Figure 4. $R_{DS(ON)}$ vs junction temperature

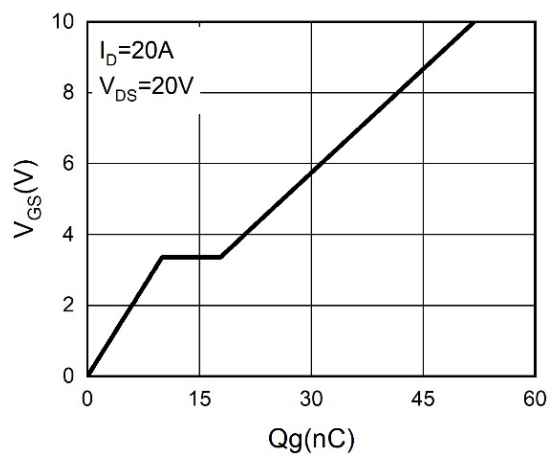


Figure 5. Gate charge waveforms

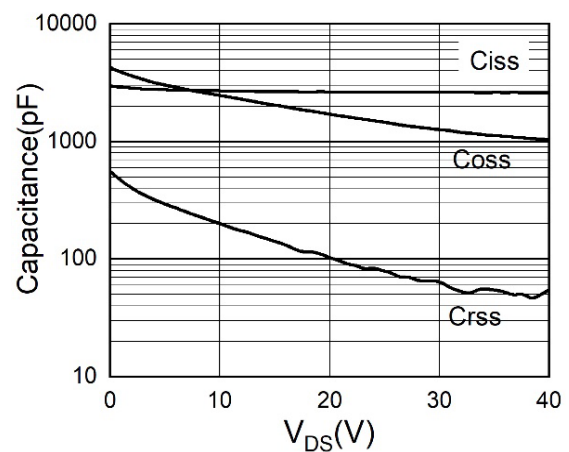
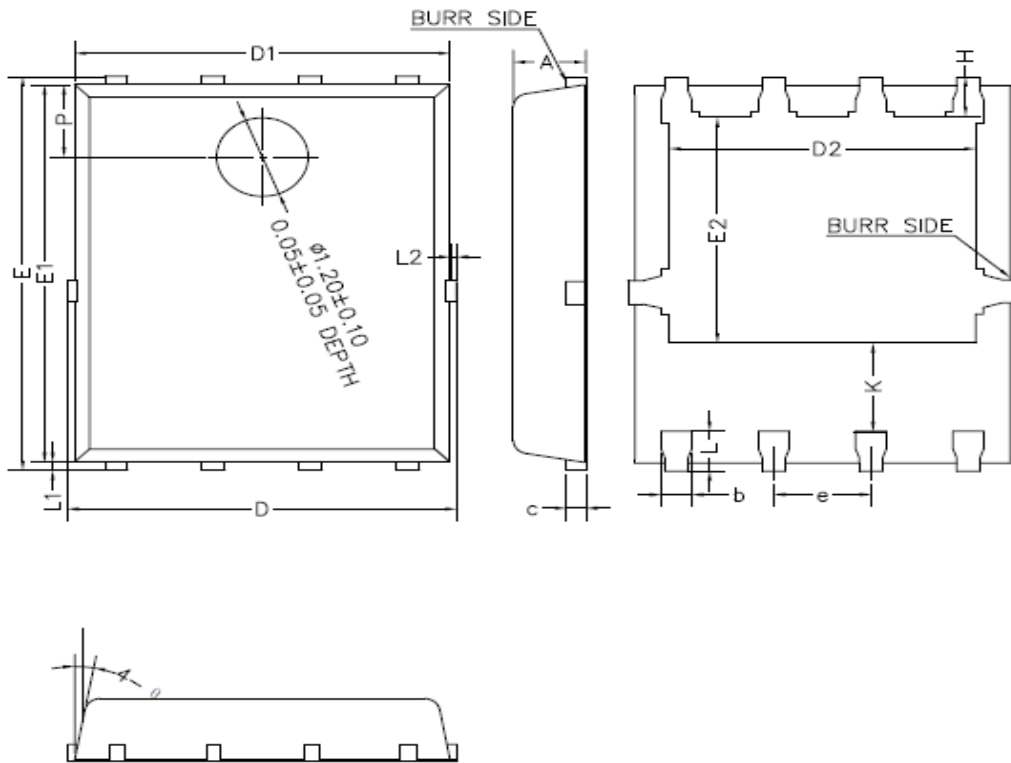


Figure 6. Capacitance

Package Information



Symbol	mm		
	Min.	Typ.	Max.
A	1.000	1.100	1.200
b	0.35	0.40	0.45
c	0.21	0.25	0.34
D	-	-	5.100
D1	4.900	4.950	5.000
D2	3.910	4.010	4.110
e	1.17	1.27	1.37
E	5.900	6.000	6.100
E1	5.700	5.750	5.800
E2	3.340	3.440	3.540
H	0.510	0.610	0.710
K	1.100	-	-
L	0.510	0.610	0.710
L1	0.060	0.130	0.200
L2	-	-	0.150
P	1.00	1.10	1.20
θ	8°	10°	12°

Version: PDFN5X6-G package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
PDFN5X6-G	5000	2	10000	6	60000

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